TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC259AP,TC74HC259AF,TC74HC259AFN

8-Bit Addressable Latch

The TC74HC259A is a high speed CMOS ADDRESSABLE LATCH fabricated with silicon gate C²MOS technology.

It achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The respective bits are controlled by address inputs A, B, and C. When $\overrightarrow{\text{CLEAR}}$ input is held high and enable input G is held low, the data is written into the bit selected by address inputs, the other bit hold their previous conditions.

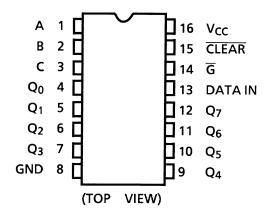
When both $\overline{\text{CLEAR}}$ and $\overline{\text{G}}$ held high, writing of all bits is inhibited regardless of adress inputs, and their previous condition are held. When $\overline{\text{CLEAR}}$ is held low and $\overline{\text{G}}$ is held high, all bits are resent to low regardless of the other inputs. When both of $\overline{\text{CLEAR}}$ and $\overline{\text{G}}$ held low, all bits which isn't selected by adress inputs are resent to low.

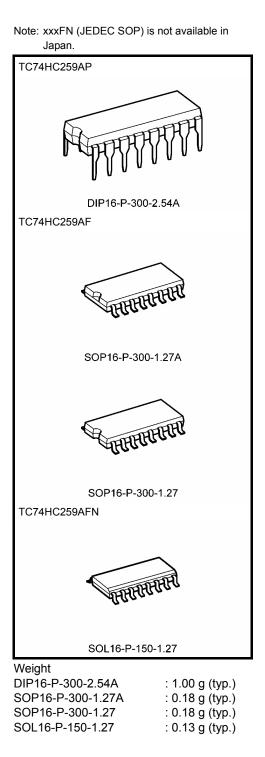
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: $t_{pd} = 15 \text{ ns}$ (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \pmod{at Ta} = 25^{\circ}C$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 4 mA (min)
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2~6 V
- Pin and function compatible with 74LS259

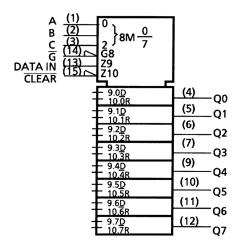
Pin Assignment





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IEC Logic Symbol



Truth Table

Inputs		Output of Addressed	Each Other	Function
CLEAR	IG	Latch Output		runction
Н	L	D	QiO	Addressable Latch
н	Н	QiO	QiO	Memory
L	L	D	L	8-Line Demultriplexer
L	H L		L	Clear All Bits to "L"

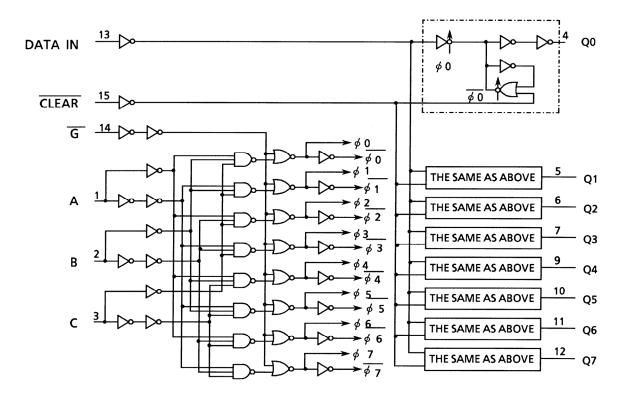
Se	elect Inpu	uts	Latch Addressed				
С	В	А	Laich Addressed				
L	L	L	Q0				
L	L	Н	Q1				
L	Н	L	Q2				
L	Н	Н	Q3				
Н	L	L	Q4				
Н	L	Н	Q5				
н	н	L	Q6				
н	н	н	Q7				

D: The level at the data input.

QiO: The level before the indicared steady-state input conditions were established (i = 0, 1, 7)

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System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~V _{CC} + 0.5	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	lıк	±20	mA
Output diode current	IOK	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of $Ta = -40 \sim 65^{\circ}C$. From Ta = 65 to $85^{\circ}C$ a derating factor of -10 mW/°C should be applied until 300 mW.

Recommended Operating Conditions (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2~6	V
Input voltage	VIN	0~V _{CC}	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
		0~1000 (V _{CC} = 2.0 V)	
Input rise and fall time	t _r , t _f	0~500 (V _{CC} = 4.5 V)	ns
		0~400 (V _{CC} = 6.0 V)	

Note: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Oh erre de niediere		Test Condition			-	Ta = 25°C		Ta = -4		
Characteristics	acteristics Symbol				Min	Тур.	Max	Min	Max	Unit
				2.0	1.50	_	_	1.50	_	
High-level input voltage	VIH			4.5	3.15	—	—	3.15	—	V
Ũ				6.0	4.20	—	_	4.20	_	
				2.0	_	—	0.50	—	0.50	
Low-level input voltage	VIL		_	4.5	_	—	1.35	—	1.35	V
Ũ				6.0	_	—	1.80	_	1.80	
	Vон	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -20 μA	2.0	1.9	2.0	_	1.9		
				4.5	4.4	4.5	—	4.4	—	
High-level output voltage				6.0	5.9	6.0	_	5.9		V
Ũ			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31		4.13		
			I _{OH} = -5.2 mA	6.0	5.68	5.80	_	5.63	_	
	V _{OL}	V _{IN} = V _{IH} or		2.0	_	0.0	0.1	_	0.1	
			$I_{OL} = 20 \ \mu A$	4.5	—	0.0	0.1	—	0.1	
Low-level output voltage				6.0	_	0.0	0.1	_	0.1	V
, , , , , , , , , , , , , , , , , , ,		VIL	$I_{OL} = 4 \text{ mA}$	4.5	—	0.17	0.26	—	0.33	
			I _{OL} = 5.2 mA	6.0	_	0.18	0.26	_	0.33	
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0	_	_	±0.1		±1.0	μA
Quiescent supply current	Icc	$V_{IN} = V_C$	_C or GND	6.0	_	_	4.0	_	40.0	μA

Timing Requirements (input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition	Test Condition			Ta = _40 ~85°C	Unit	
			V _{CC} (V)	Тур.	Limit	Limit		
Minimum pulse width			2.0	_	75	95		
(\overline{G})	t _{W (L)}	—	4.5	—	15	19	ns	
(6)			6.0		13	16		
Minimum pulse width			2.0		75	95		
(CLEAR)	t _{W (L)}	—	4.5	—	15	19	ns	
			6.0	_	13	16		
Minimum set-up time			2.0	—	50	60		
(DATA)	ts	—	4.5	—	10	12	ns	
			6.0	_	9	11		
Minimum set-up time			2.0	—	25	30		
(A, B, C)	t _s	—	4.5	—	5	6	ns	
(,, ,, , ,)			6.0	_	5	5		
Minimum hold time			2.0	—	25	30		
(DATA)	t _h	—	4.5	—	5	6	ns	
			6.0	_	5	5		
Minimum hold time			2.0	—	0	0		
(A, B, C)	t _h	—	4.5	—	0	0	ns	
(,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			6.0	—	0	0		

AC Characteristics (C_L = 15 pF, V_{CC} = 5 V, Ta = 25°C, input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Output transition time	tтLH tтнL	_	_	4	8	ns
Propagation delay time (DATA-Q)	t _{pLH} t _{pHL}	_	_	15	22	ns
Propagation delay time (A, B, C-Q)	^t pLH t _{pHL}	_		21	32	ns
Propagation delay time $(\overline{G} - Q)$	t _{pLH} t _{pHL}	_	_	16	28	ns
Propagation delay time (CLEAR -Q)	t _{pHL}	_	_	13	23	ns

AC Characteristics (C_L = 50 pF, input: $t_r = t_f = 6 \text{ ns}$)

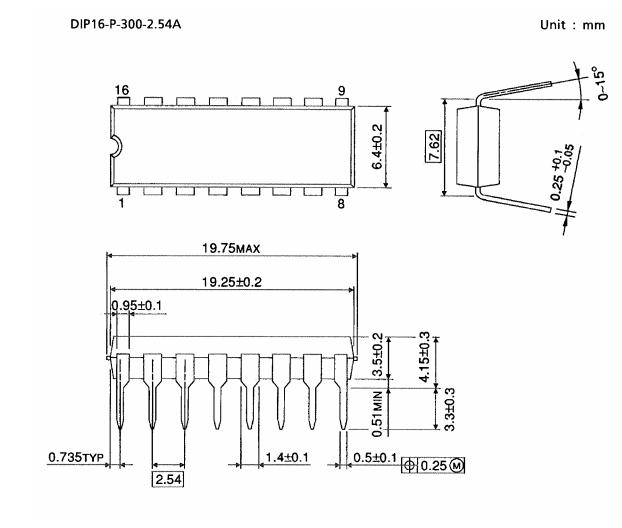
		Test Condition		-	Га = 25°С)	Ta = -4		
Characteristics	Symbol		V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
	4		2.0	_	30	75	_	95	
Output transition time	t _{TLH}	_	4.5	—	8	15	—	19	ns
	t _{THL}		6.0	—	7	13	—	16	
Propagation delay	+		2.0	_	56	130	_	165	
time	t _{pLH}	—	4.5	—	18	26	—	33	ns
(DATA-Q)	t _{pHL}		6.0	—	15	22	—	28	
Propagation delay	+		2.0	_	83	185	_	230	
time	t _{pLH}	—	4.5	—	25	37	—	46	ns
(A, B, C-Q)	t _{pHL}		6.0	—	21	31	—	39	
Propagation delay	+		2.0	_	67	165	_	205	
time	t _{pLH}	_	4.5	—	20	33	—	41	ns
(G -Q)	t _{pHL}		6.0	—	17	28	—	35	
Propagation delay			2.0	_	52	135	_	170	
time	t _{pHL}	—	4.5	—	16	27	—	34	ns
(CLEAR -Q)			6.0	—	14	23	—	29	
Input capacitance	C _{IN}	_		_	5	10	_	10	pF
Power dissipation	C _{PD}				35				nE
capacitance	(Note)				30				pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

Package Dimensions



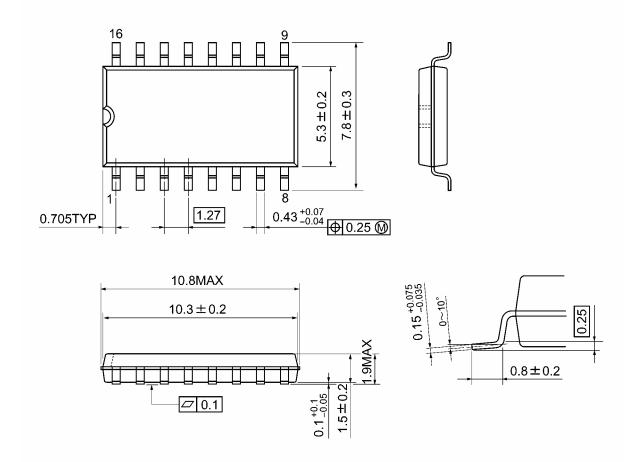
Weight: 1.00 g (typ.)



Package Dimensions

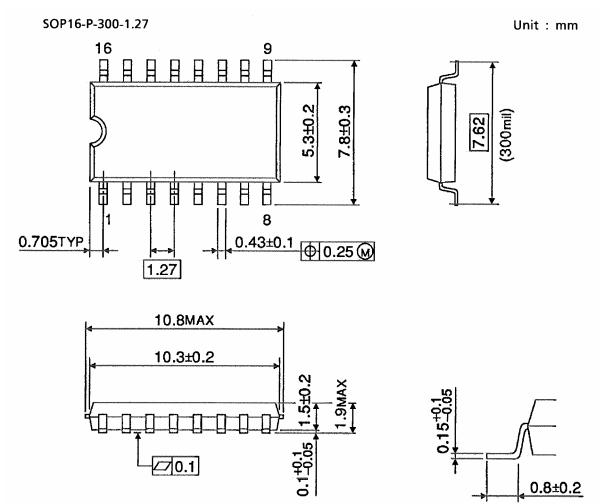
SOP16-P-300-1.27A

Unit: mm



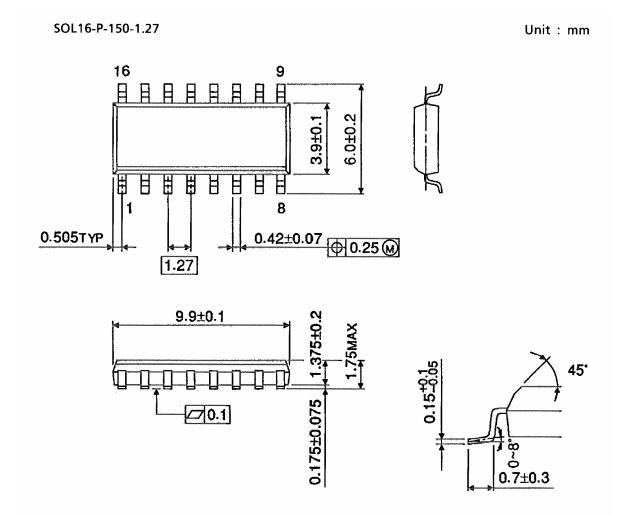
Weight: 0.18 g (typ.)

Package Dimensions



Weight: 0.18 g (typ.)

Package Dimensions (Note)



Note: This package is not available in Japan.

Weight: 0.13 g (typ.)

Note: Lead (Pb)-Free Packages DIP16-P-300-2.54A SOP16-P-300-1.27A SOL16-P-150-1.27

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